Electronic Supplementary Information

Silver Nanowire-embedded PDMS with Multiscale Structure for Highly Sensitive and Robust Flexible Pressure Sensor

Yunsik Joo, Junghwan Byun, Narkhyeon Seong, Jewook Ha, Hyunjong Kim, Sangwoo Kim, Taehoon Kim, Hwarim Im, Donghyun Kim and Yongtaek Hong

*Department of Electrical and Computer Engineering
Inter University Semiconductor Research Center (ISRC)
Seoul National University
Seoul, 151–742, Republic of Korea
E-mail: yongtaek@snu.ac.kr
Figure S1. The microstructure of the AgNW-embedded multiscale-structured PDMS electrode. (a) 3-D surface profiler image shows the multiscale structure of the AgNW-embedded PDMS electrode. (b) Top view SEM images of the AgNW-embedded PDMS electrode. SEM images show the rough surface of the crest. (c) AFM image and line profile of the trough of the multiscale-structured electrode. The root-mean-square (RMS) value of the measured line roughness at the trough is about 25 nm.
Figure S2. (a) The resistance change of the multiscale-structured electrode during the repeated loading/unloading of the pressure of 10 kPa. (b) The microscopic images of the as-prepared multiscale-structured electrode and the multiscale-structured electrode after 80-cycle test, respectively.
Figure S3. Relative capacitance change-pressure curves from the consecutive loading-unloading cycles.
Figure S4. The capacitance-pressure curve of the pressure sensor. We tested ten independent samples and the error bars represent the standard deviation from ten samples.
Figure S5. (a,b) Microscopic images of the multiscale-structured electrode obtained from the mould with pre-strain level of 25%. The average wavelength and amplitude are about 25 μm and 5 μm, respectively. (c,d) Microscopic images of the multiscale-structured electrode obtained from the mould with pre-strain level of 55%. The average wavelength and amplitude are about 22 μm and 7 μm, respectively. (e) Relative capacitance change-pressure curve of the sensors from the mould PDMS with different pre-strain level.
Figure S6. The pressure sensor with oxide dielectric layer. (a) Schematic diagram of the pressure sensor fabricated with the multiscale-structured electrode, SiO$_2$ dielectric layer (thermally grown, 200 nm) and p+ silicon substrate (b) Pressure-response curves of the pressure sensor.